

## **Amendments to the Specification**

*Please replace paragraph [0070] with the following amended paragraph:*

**[0070]** The semiconductor wafer cleaning apparatus also includes a gas spraying unit 15 for spraying gas towards the wafer, and a gas supply means for supplying gases to the gas spraying unit 15. The gas supply means includes gas supply sources G, a gas line 17a, valves V1 through V4 and V7 through V9, mass flow controllers MFC1 through MFC5, gas measuring gauges M1 and M2, and a mixer 17b. For ease of explanation, only four gas supply sources G1 through G4 are illustrated although more may be provided. The mixer 17b mixes gases supplied from the gas supply sources G1 through G4 and supplies the mixed gases to the gas spraying unit 15. Gases not used among the gases supplied from the gas supply sources G1 through G4 are exhausted by a vacuum pump 21.

*Please replace paragraph [0135] with the following amended paragraph:*

**[0135]** Next, the water layer on the cleaned wafer is dried (step 140). The water layer is dried by spraying isopropyl alcohol (IPA) onto the rotating wafer using the gas spraying unit [14] 15. Therefore, that segment of the method from the cleaning step to the drying step can be performed in the same chamber 11. [-]